

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	3734	"trench capacitor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	187	1 and (polysilicon near7 arsenic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	142	@ad<=20000707 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	109	3 and (CVD or ALD or ALCVD or "atomic layer deposition" or "atomic layer chemical vapor deposition" or "chemical vapor deposition")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB